

2SB1493

Silicon PNP epitaxial planar type Darlington

For power amplification

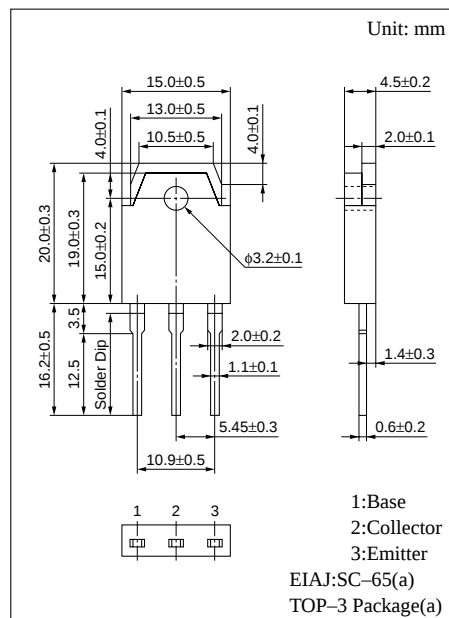
Complementary to 2SD2255

Features

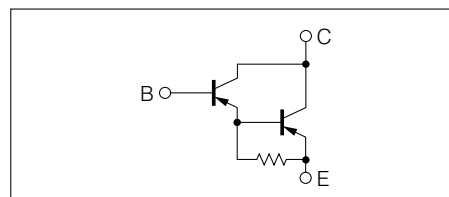
- Optimum for 60W HiFi output
- High forward current transfer ratio h_{FE} : 5000 to 30000
- Low collector to emitter saturation voltage $V_{CE(sat)}$: $< -2.5V$

Absolute Maximum Ratings ($T_C=25^\circ C$)

Parameter		Symbol	Ratings	Unit
Collector to base voltage		V_{CBO}	−160	V
Collector to emitter voltage		V_{CEO}	−140	V
Emitter to base voltage		V_{EBO}	−5	V
Peak collector current		I_{CP}	−12	A
Collector current		I_C	−7	A
Collector power dissipation	$T_C=25^{\circ}C$	P_C	70	W
	$T_a=25^{\circ}C$		2.5	
Junction temperature		T_j	150	$^{\circ}C$
Storage temperature		T_{stg}	−55 to +150	$^{\circ}C$



Internal Connection



Electrical Characteristics ($T_C=25^\circ C$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -160V, I_E = 0$			-100	μA
	I_{CEO}	$V_{CE} = -140V, I_B = 0$			-100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-100	μA
Collector to emitter voltage	V_{CEO}	$I_C = -30mA, I_B = 0$	-140			V
Forward current transfer ratio	h_{FE1}	$V_{CE} = -5V, I_C = -1A$	2000			
	h_{FE2}^*	$V_{CE} = -5V, I_C = -6A$	5000		30000	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -6A, I_B = -6mA$			-2.5	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -6A, I_B = -6mA$			-3.0	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -0.5A, f = 1MHz$		20		MHz
Turn-on time	t_{on}	$I_C = -6A, I_{B1} = -6mA, I_{B2} = 6mA, V_{CC} = -50V$		1.0		μs
Storage time	t_{stg}			1.5		μs
Fall time	t_f			1.2		μs

* h_{FE2} Rank classification

Rank	Q	P
h_{FE2}	5000 to 15000	8000 to 30000

Power Transistors

2SB1493

